



CZT31C NPN
CZT32C PNP

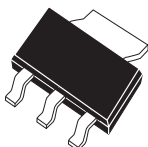
**2.0W COMPLEMENTARY SILICON
POWER TRANSISTOR**

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT31C and CZT32C types are surface mount epoxy molded complementary silicon transistors manufactured by the epitaxial base process, designed for surface mounted power amplifier applications up to 3.0 amps.

POWERTM
223



SOT-223 CASE

MAXIMUM RATINGS: (T_A=25°C)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Peak Collector Current
Base Current
Power Dissipation
Operating and Storage
Junction Temperature
Thermal Resistance

SYMBOL

V_{CB0}
V_{CEO}
V_{EBO}
I_C
I_{CM}
I_B
P_D

100
100
5.0
3.0
6.0
1.0
2.0

UNITS

V
V
V
A
A
A
W

T_J, T_{stg}
θ_{JA}

-65 to +150
62.5

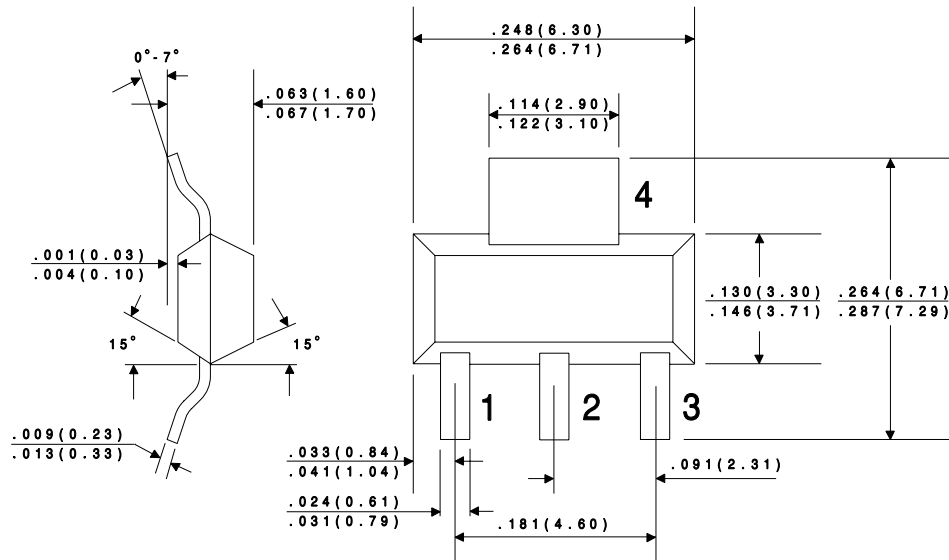
°C
°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CES}	V _{CE} =100V		200	μA
I _{CEO}	V _{CE} =60V		300	μA
I _{EBO}	V _{EB} =5.0V		1.0	mA
BV _{CEO}	I _C =30mA	100		V
* V _{CE(SAT)}	I _C =3.0A, I _B =375mA		1.2	V
* V _{BE(ON)}	V _{CE} =4.0V, I _C =3.0A		1.8	V
* h _{FE}	V _{CE} =4.0V, I _C =1.0A	25		
* h _{FE}	V _{CE} =4.0V, I _C =3.0A	10	100	
f _T	V _{CE} =10V, I _C =500mA, f=1.0MHz	3.0		MHz

* Pulsed, 2%D.C.

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR